A 9-16 GHz Monolithic HEMT Low Noise Amplifier with Embedded Limiters (1995 Vol. I [MWSYM])

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A novel 9-16 GHz monolithic HEMT low noise amplifier with on-chip limiters has been designed, fabricated, and measured. This paper presents the design topology, the new fabrication technology, and the on-wafer measurements of this circuit. The limiter consists of one PIN diode and one Schottky diode. The low noise amplifier itself is a single stage balanced amplifier with one limiter embedded in each single-ended amplifier.

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